



The Certified memory line is built to the highest standards possible, ensuring immediate system enhancements and a lifetime of reliability. Buffalo Certified memory modules are manufactured using only the latest components from leading semiconductor companies such as Samsung, Micron and Hynix. Each module is thoroughly tested in-house and endures extensive quality testing in the Motherboard Production tests, which place each module under booting and speed tests on today's most popular motherboards. Buffalo then takes testing our modules one step further by utilizing Computer Memory Test Labs (CMTL), a third party testing facility. CMTL's certification program validates the Certified modules for cross-platform compatibility and reliability with numerous motherboards, processors and chipsets.

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1333MHz 240 Pir	PC3-10600	Unbuffered x64	Non-ECC
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Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D3U1333-2G	2GB	16	x 8	2	7	1.5V
D3U1333-S1G	1GB	8	x 8	1	7	1.5V

### 1066MHz 240 Pin PC3-8500 Unbuffered x64 Non-ECC

Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D3U1066-2G	2GB	16	x 8	2	7	1.5V
D3U1066-S1G	1GB	8	x 8	1	7	1.5V

# Certified DDR2 FBDIMM:

# 800MHz 240 Pin PC2-6400 Fully Buffered x72 ECC

Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2F800CW-4G	4GB	36	x 4	2	5	1.8V
D2F800CW-2G	2GB	18	x 8	2	5	1.8V
D2F800CW-1G	1GB	18	x 8	2	5	1.8V

# 667MHz 240 Pin PC2-5300 Fully Buffered x72 ECC

Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2F667CW-2G	2GB	36	x 4	2	5	1.8V
D2F667CW-1G	1GB	18	x 8	2	5	1.8V

# Certified DDR2 DIMM:

# 800MHz 240 Pin PC2-6400 Unbuffered x64 Non-ECC

Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage	
D2U800C-2G	2GB	16	x 8	2	5	1.8V	
D2U800C-1G	1GB	16	x 8	2	5	1.8V	
D2U800C-S1G	1GB	8	x 8	1	5	1.8V	
D2U800CX-2G	2GB	16	x 8	2	5	1.8V	
D2U800CX-1G	1GB	16	x 8	2	5	1.8V	
D2U800CX-S1G	1GB	8	x 8	1	5	1.8V	

### 800MHz 240 Pin PC2-6400 Unbuffered x72 ECC

Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2U800C-E2G	2GB	18	x 8	1	5	1.8V
D2U800C-ES1G	1GB	9	x 8	1	5	1.8V

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667MHz 240 Pin P	C2-5300 Unbut	fered x64 Non-E0	CC			
Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2U667C-2G	2GB	16	x 8	2	5	1.8V
D2U667C-1G	1GB	16	x 8	2	5	1.8V
D2U667C-S1G	1GB	8	x 8	1	5	1.8V
D2U667C-S512	512MB	8	x 8	1	5	1.8V
667MHz 240 Pin P	C2-5300 Unbuf					
Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2U667C-E2G	2GB	18	x 8	2	5	1.8V
D2U667C-ES1G	1GB	9	x 8	1	5	1.8V
667MHz 240 Pin PC	22-5300 Fully R	uffered v72 FCC				
			Type	Rank	CASLatonov	Voltago
Part #	Capacity	Chip Count	Type		CAS Latency	Voltage
D2R667C-E2G	2GB	18	x 8	2	5	1.8V
D2R667C-ES1G	1GB	9	x 8	1	5	1.8V
533MHz 240 Pin P	C2-4200 Unbuf	fered x64 Non-E0				
Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2U533B-1G	1GB	16	x 8	2	4	1.8V
D2U533B-S512	512MB	8	x 8	1	4	1.8V
D20333D 3312	3121110		χ σ	•		1.01
533MHz 240 Pin P	C2-4200 Unbuf	fered x72 ECC				
Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2U533B-E1G	1GB	18	x 8	2	4	1.8V
D2U533B-ES512	512MB	9	x 8	1	4	1.8V
		1 == ===				
533MHz 240 Pin P						
Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
D2R533B-E1G	2GB	18	x 8	2	4	1.8V
D2R533B-ES512	512MB	9	x 8	1	4	1.8V
Certified DDR1 D	DIMM:					
400MHz 184 Pin P		ered x64 Non-EC0				
		Chip Count	Type	Rank	CAS Latency	Voltage
DD4333-1G	1GB	16	x 8	2	3	2.6V
DD4333-512	512MB	16	x 8	2	3	2.6V
DD4333-S512	512MB	8	x 8	_ 1	3	2.6V
DD4333-X256	512MB	4	x 16	1	3	2.6V
400MHz 184 Pin P						
Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
DD4333-E1G	1GB	18	x 8	2	3	2.6V
DD4333-ES512	512MB	9	x 8	1	3	2.6V
400MHz 184 Pin P	C-3200 Registe	red x72 FCC			7	
Part #	Capacity	Chip Count	Type	Rank	CAS Latency	Voltage
DD4333L-R1G	1GB	18	x 8		•	2.6V
DD4333L-R1G DD4333L-R512	512MB	18	x 8	2	3 3	2.6V 2.6V
DD4333F-K315	JIZIVID	10	λ Ο	۷	3	Z.UV